

each of said pair of regions has a first portion contiguous to the channel region and a second portion contiguous to the source or drain regions;

a gate insulating film formed over said semiconductor region;

61 a first conductive layer formed over the channel region with the gate insulating film interposed therebetween; and

a second conductive layer formed on said first conductive layer wherein a width of the first conductive layer is narrower than that of the second conductive layer;

wherein the second conductive layer extends beyond side edges of the first conductive layer and extending portions of the second conductive layer overlap the first portions of said pair of regions while the second portions are not overlapped by said second conductive layer.

Please add new claims 44-84 as follows.

44. (NEW) A semiconductor device comprising:

62 a semiconductor film comprising a source region, a drain region, a channel region formed on an insulating surface, and a pair of regions between the channel region and the source and drain regions, said pair of regions formed of a same material as

said channel region wherein each of said pair of regions has a first portion contiguous to the channel region and a second portion contiguous to the source or drain regions;

a gate insulating film formed over the semiconductor region;

a first conductive layer formed over the channel region with the gate insulating film interposed therebetween; and

G2 a second conductive layer formed on the first conductive layer wherein a width of the first conductive layer is narrower than a width of the second conductive layer,

wherein the second conductive layer extends beyond side edges of the first conductive layer and extending portions of the second conductive layer overlap the first portions of said pair of regions while the second portions are not overlapped by said second conductive layer.

45. (NEW) A semiconductor device comprising:

a semiconductor region comprising a source region, a drain region, a channel region, and a pair of regions between the channel region and the source and drain regions, said pair of regions are formed of a same material as said channel region, wherein each of said pair of regions has a first portion

contiguous to the channel region and a second portion contiguous to the source or drain regions;

a gate insulating film formed over the semiconductor region;

a first conductive layer formed over the channel region with the gate insulating film interposed therebetween; and

a second conductive layer formed on the first conductive layer, wherein a width of the first conductive layer is narrower than a width of the second conductive layer,

62 wherein the second conductive layer extends beyond side edges of the first conductive layer and extending portions of the second conductive layer overlap the first portions of said pair of regions while the second portions are not overlapped by said second conductive layer, and

wherein a distance between the first portion and the source or drain region is larger than a thickness of the first conductive layer.

46. (NEW) A semiconductor device comprising:

a semiconductor film comprising a source region, a drain region, a channel region formed on an insulating surface, and a pair of regions between the channel region and the source and drain regions, said pair of regions formed of a same material as

said channel region wherein each of said pair of regions has a first portion contiguous to the channel region and a second portion contiguous to the source or drain regions;

a gate insulating film formed over the semiconductor region;

a first conductive layer formed over the channel region with the gate insulating film interposed therebetween; and

G2 a second conductive layer formed on the first conductive layer, wherein a width of the first conductive layer is narrower than that of the second conductive layer,

wherein the second conductive layer extends beyond side edges of the first conductive layer and extending portions of the second conductive layer overlap the first portions of said pair of regions while the second portions are not overlapped by said second conductive layer, and

wherein a distance between the first portion and the source or drain region is larger than a thickness of the first conductive layer.

47. (NEW) A semiconductor device comprising:

a semiconductor region comprising a source region, a drain region, a channel region, and a pair of regions between the channel region and the source and drain regions, said pair of

regions formed of a same material as said channel region wherein each of said pair of regions has a first portion contiguous to the channel region and a second portion contiguous to the source or drain regions;

a gate insulating film formed over the semiconductor region;

a first conductive layer formed over the channel region with the gate insulating film interposed therebetween; and

Gd a second conductive layer formed on the first conductive layer wherein a width of the first conductive layer is narrower than that of the second conductive layer,

wherein the second conductive layer extends beyond side edges of the first conductive layer and extending portions of the second conductive layer overlap the first portions of said pair of regions while the second portions are not overlapped by said second conductive layer, and

wherein a distance between the first portion and the source or drain region is equal to or less than a thickness of the first conductive layer.

48. (NEW) A semiconductor device comprising:

a semiconductor film comprising a source region, a drain region, a channel region formed on an insulating surface, and a

pair of regions between the channel region and the source and drain regions, said pair of regions formed of a same material as said channel region, wherein each of said pair of regions has a first portion contiguous to the channel region and a second portion contiguous to the source or drain regions;

a gate insulating film formed over the semiconductor region;

a first conductive layer formed over the channel region with the gate insulating film interposed therebetween; and

G2 a second conductive layer formed on the first conductive layer wherein a width of the first conductive layer is narrower than that of the second conductive layer,

wherein the second conductive layer extends beyond side edges of the first conductive layer and extending portions of the second conductive layer overlap the first portions of said pair of regions while the second portions are not overlapped by said second conductive layer, and

wherein a distance between the first portion and the source or drain region is equal to or less than a thickness of the first conductive layer.

49. (NEW) A semiconductor device according to claim 1,

wherein a anodic oxide layer is formed on at least side surface of the first conductive layer and side surface of the second conductive layer.

50. (NEW) A semiconductor device according to claim 44, wherein a anodic oxide layer is formed on at least side surface of the first conductive layer and side surface of the second conductive layer.

62 51. (NEW) A semiconductor device according to claim 45, wherein an anodic oxide layer is formed on at least side surfaces of the first conductive layer and side surfaces of the second conductive layer.

52. (NEW) A semiconductor device according to claim 46, wherein an anodic oxide layer is formed on at least side surfaces of the first conductive layer and side surfaces of the second conductive layer.

53. (NEW) A semiconductor device according to claim 47, wherein an anodic oxide layer is formed on at least side surfaces of the first conductive layer and side surfaces of the second conductive layer.

54. (NEW) A semiconductor device according to claim 48, wherein an anodic oxide layer is formed on at least side surfaces of the first conductive layer and side surfaces of the second conductive layer.

32 55. (NEW) A semiconductor device according to claim 1, wherein each of the first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt.

56. (NEW) A semiconductor device according to claim 44, wherein each of the first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt.

57. (NEW) A semiconductor device according to claim 45, wherein each of the first and second conductive layers comprises a material selected from the group consisting of

molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt.

58. (NEW) A semiconductor device according to claim 46, wherein each of the first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt.

69 59. (NEW) A semiconductor device according to claim 47, wherein each of the first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt.

60. (NEW) A semiconductor device according to claim 48, wherein each of the first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt.

61. (NEW) A semiconductor device according to claim 1,

wherein a distance between the first portion and the source or drain region is 500. to 1000..

62. (NEW) A semiconductor device according to claim 44, wherein a distance between the first portion and the source or drain region is 500Å to 1000Å.

63. (NEW) A semiconductor device according to claim 45, wherein a distance between the first portion and the source or drain region is 500Å to 1000Å.

64. (NEW) A semiconductor device according to claim 46, wherein a distance between the first portion and the source or drain region is 500Å to 1000Å.

65. (NEW) A semiconductor device according to claim 47, wherein a distance between the first portion and the source or drain region is 500Å to 1000Å.

66. (NEW) A semiconductor device according to claim 48, wherein a distance between the first portion and the source or drain region is 500Å to 1000Å.

67. (NEW) A semiconductor device according to claim 1, wherein said gate insulating film comprises silicon oxide.

68. (NEW) A semiconductor device according to claim 44, wherein said gate insulating film comprises silicon oxide.

69. (NEW) A semiconductor device according to claim 45, wherein said gate insulating film comprises silicon oxide.

62 70. (NEW) A semiconductor device according to claim 46, wherein said gate insulating film comprises silicon oxide.

71. (NEW) A semiconductor device according to claim 47, wherein said gate insulating film comprises silicon oxide.

72. (NEW) A semiconductor device according to claim 48, wherein said gate insulating film comprises silicon oxide.

73. (NEW) A semiconductor device according to claim 1, wherein said first conductive layer comprises tantalum and said second conductive layer comprises aluminum.

74. (NEW) A semiconductor device according to claim 44, wherein said first conductive layer comprises tantalum and said second conductive layer comprises aluminum.

75. (NEW) A semiconductor device according to claim 45, wherein said first conductive layer comprises tantalum and said second conductive layer comprises aluminum.

67d 76. (NEW) A semiconductor device according to claim 46, wherein said first conductive layer comprises tantalum and said second conductive layer comprises aluminum.

77. (NEW) A semiconductor device according to claim 47, wherein said first conductive layer comprises tantalum and said second conductive layer comprises aluminum.

78. (NEW) A semiconductor device according to claim 48, wherein said first conductive layer comprises tantalum and said second conductive layer comprises aluminum.

79. (NEW) A semiconductor device according to claim 1, wherein the semiconductor region comprises crystalline silicon.

80. (NEW) A semiconductor device according to claim 44,
wherein the semiconductor film comprises crystalline silicon.

81. (NEW) A semiconductor device according to claim 45,
wherein the semiconductor region comprises crystalline silicon.

G2 82. (NEW) A semiconductor device according to claim 46,
wherein the semiconductor film comprises crystalline silicon.

83. (NEW) A semiconductor device according to claim 47,
wherein the semiconductor region comprises crystalline silicon.

84. (NEW) A semiconductor device according to claim 48,
wherein the semiconductor film comprises crystalline silicon.
